



## PRODUCT DATA SHEET

To learn more about JGSEMI, please visit our website at



**Datasheet**



**Resources**

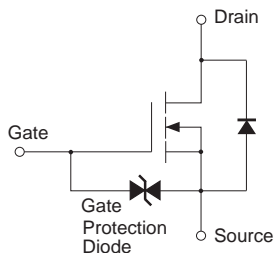


**Samples**

Please note: Please check the JINGAO Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at [www.jg-semi.cn](http://www.jg-semi.cn). Please email any questions regarding the system integration to [JINGAO\\_questions@jgsemi.com](mailto:JINGAO_questions@jgsemi.com).

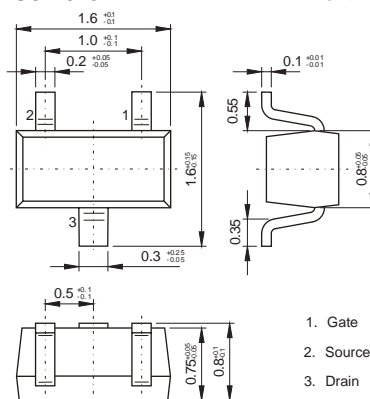
## ■ Features

- Low on-resistance.
- Fast switching speed.
- Low voltage drive (2.5V) makes this device ideal for portable equipment.
- Easily designed drive circuits.
- Easy to parallel.



SOT-523

Unit : mm



## ■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V <sub>DS</sub>	30	V
Gate-Source Voltage	V <sub>GS</sub>	±20	
Continuous Drain Current	I <sub>D</sub>	±100	mA
Continuous Drain Current Pulsed *1	I <sub>DP</sub>	±400	
Power Dissipation *2	P <sub>D</sub>	150	mW
Junction Temperature	T <sub>J</sub>	150	°C
Storage Temperature Range	T <sub>stg</sub>	-55 to 150	

\*1 P<sub>w</sub> ≤ 10μs, Duty cycle ≤ 1%

\*2 With each pin mounted on the recommended lands.

## ■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V <sub>BSS</sub>	I <sub>D</sub> =100μA, V <sub>GS</sub> =0V	30			V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =30V, V <sub>GS</sub> =0V			1	μA
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>DS</sub> =0V, V <sub>GS</sub> =±20V			±1	μA
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =100μA	0.8		1.5	V
Static Drain-Source On-Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =4V, I <sub>D</sub> =10mA		5	8	Ω
		V <sub>GS</sub> =2.5V, I <sub>D</sub> =1mA		7	13	
Forward Transfer admittance	Y <sub>fs</sub>	V <sub>DS</sub> =3V, I <sub>D</sub> =10mA	20			mS
Input Capacitance	C <sub>iss</sub>	V <sub>GS</sub> =0V, V <sub>DS</sub> =5V, f=1MHz		13		pF
Output Capacitance	C <sub>oss</sub>			9		
Reverse Transfer Capacitance	C <sub>rss</sub>			4		
Turn-On DelayTime	t <sub>d(on)</sub>	V <sub>GS</sub> =5V, V <sub>DS</sub> =5V, R <sub>L</sub> =500Ω, R <sub>GEN</sub> =10Ω  I <sub>D</sub> =10mA		15		ns
Turn-On Rise Time	t <sub>r</sub>			35		
Turn-Off DelayTime	t <sub>d(off)</sub>			80		
Turn-Off Fall Time	t <sub>f</sub>			80		

## ■ Typical Characteristics

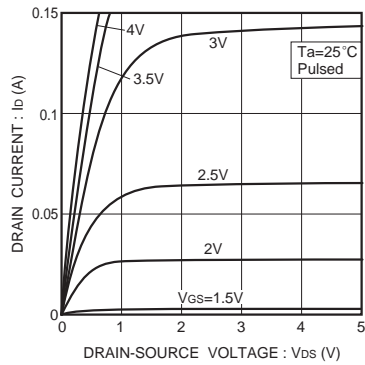


Fig.1 Typical output characteristics

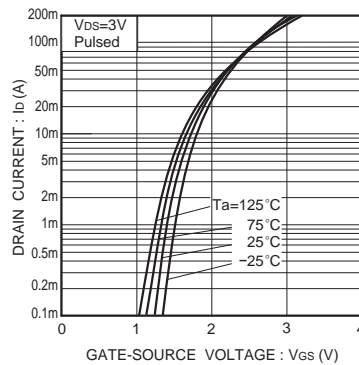


Fig.2 Typical transfer characteristics

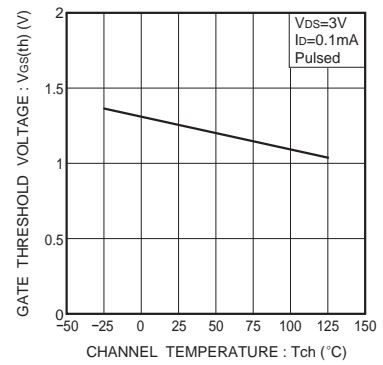


Fig.3 Gate threshold voltage vs. channel temperature

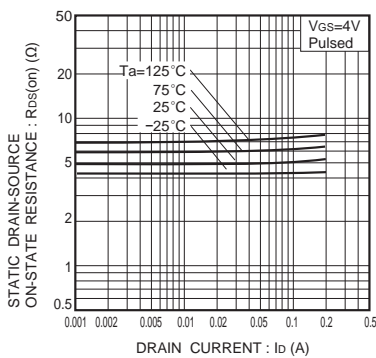


Fig.4 Static drain-source on-state resistance vs. drain current (I)

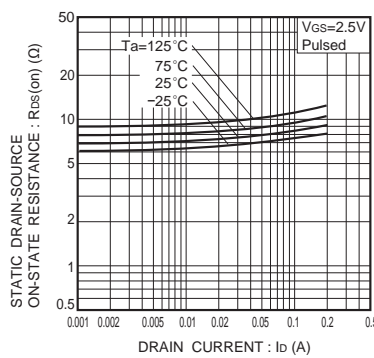


Fig.5 Static drain-source on-state resistance vs. drain current (II)

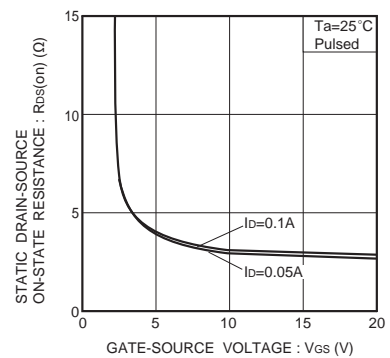


Fig.6 Static drain-source on-state resistance vs. gate-source voltage

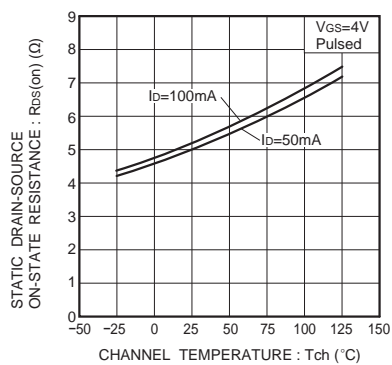


Fig.7 Static drain-source on-state resistance vs. channel temperature

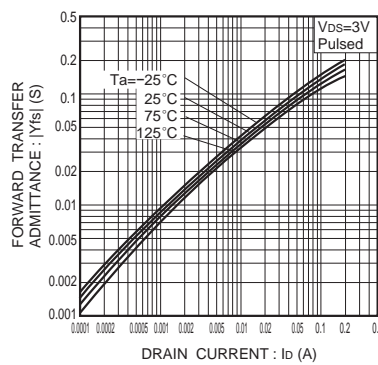


Fig.8 Forward transfer admittance vs. drain current

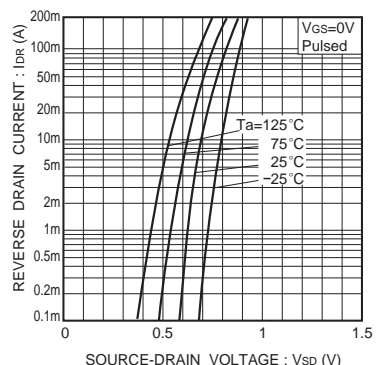


Fig.9 Reverse drain current vs. source-drain voltage (I)

### ■ Typical Characteristics

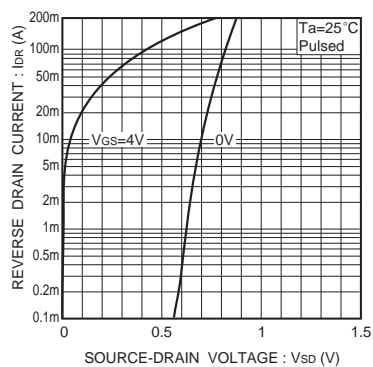


Fig.10 Reverse drain current vs. source-drain voltage (II)

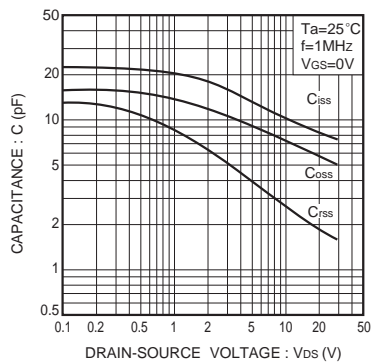


Fig.11 Typical capacitance vs. drain-source voltage

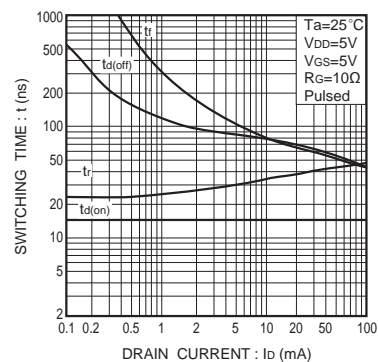


Fig.12 Switching characteristics

## Attention

1, Any and all JGSEMI products described or contained herein do not have specifications that can handle applications that require extremely high levels of reliability, such as life-support systems, aircraft's control systems, or other applications whose failure can be reasonably expected to result in serious physical or material damage. Consult with your JGSEMI representative nearest you before using any JGSEMI products described or contained herein in such applications.

2, JGSEMI assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all JGSEMI products described or contained herein.

3, Specifications of any and all JGSEMI products described or contained herein stipulate the performance, characteristics, and functions of the described products in the independent state, and are not guarantees of the performance, characteristics, and functions of the described products as mounted in the customer's products or equipment. To verify symptoms and states that cannot be evaluated in an independent device, the customer should always evaluate and test devices mounted in the customer's products or equipment.

4, In the event that any or all JGSEMI products (including technical data, services) described or contained herein are controlled under any of applicable local export control laws and regulations, such products must not be exported without obtaining the export license from the authorities concerned in accordance with the above law.

5, No part of this publication may be reproduced or transmitted in any form or by any means, electronic or mechanical, including photocopying and recording, or any information storage or retrieval system, or otherwise, without the prior written permission of JGSEMI Semiconductor CO., LTD.

6, Any and all information described or contained herein are subject to change without notice due to product technology improvement, etc. When designing equipment, refer to the "Delivery Specification" for the JGSEMI product that you intend to use.